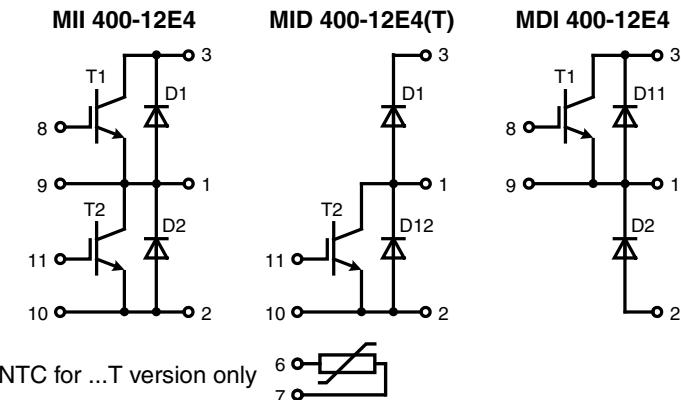


IGBT Module

phaseleg and chopper topologies
with optional temperature sensor

Preliminary Data

I_{C25} = 420 A
 V_{CES} = 1200 V
 $V_{CE(sat)\text{ typ.}}$ = 2.2 V

**IGBTs T1 - T2**

Symbol	Conditions	Maximum Ratings		
V_{CES}	$T_{VJ} = 25^\circ\text{C}$ to 125°C	1200	V	
V_{GES}		± 20	V	
I_{C25}	$T_C = 25^\circ\text{C}$	420	A	
I_{C80}	$T_C = 80^\circ\text{C}$	300	A	
I_{CM}	$V_{GE} = \pm 15\text{ V}$; $R_G = 4.7\text{ }\Omega$; $T_{VJ} = 125^\circ\text{C}$	450	A	
V_{CEK}	RBSOA Clamped inductive load; $L = 100\text{ }\mu\text{H}$	V_{CES}		
t_{SC} (SCSOA)	$V_{CE} = 900\text{ V}$; $V_{GE} = \pm 15\text{ V}$; $R_G = 4.7\text{ }\Omega$ $T_{VJ} = 125^\circ\text{C}$; non-repetitive	10	μs	
P_{tot}	$T_C = 25^\circ\text{C}$	1700	W	

Symbol **Conditions****Characteristic Values**(T_{VJ} = 25°C, unless otherwise specified)

		min.	typ.	max.	
$V_{CE(sat)}$	$I_C = 300\text{ A}$; $V_{GE} = 15\text{ V}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		2.2 2.6	2.8	V
$V_{GE(th)}$	$I_C = 10\text{ mA}$; $V_{GE} = V_{CE}$	4.5		6.5	V
I_{CES}	$V_{CE} = V_{CES}$; $V_{GE} = 0\text{ V}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		0.8 3.5	3.3	mA
I_{GES}	$V_{CE} = 0\text{ V}$; $V_{GE} = \pm 20\text{ V}$			600	nA
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^\circ\text{C}$ $V_{CE} = 600\text{ V}$; $I_C = 300\text{ A}$ $V_{GE} = \pm 15\text{ V}$; $R_G = 4.7\text{ }\Omega$		170 60 680 50 44 30		ns ns ns ns mJ mJ
C_{ies}			17		nF
Q_{Gon}			1.74		μC
R_{thJC}				0.08	K/W
R_{thJH}			0.15		K/W

Features

- NPT³ IGBT
 - low saturation voltage
 - positive temperature coefficient
 - fast switching
 - short tail current for optimized performance in resonant circuits
- HiPerFRED™ diodes
 - fast and soft reverse recovery
 - low operating forward voltage
 - low leakage current
- NTC sensor for measurement of case temperature
- Package
 - low inductive current path
 - screw connection to high current main terminals
 - use of non interchangeable connectors for auxiliary terminals possible
 - Kelvin emitter terminal for easy drive
 - isolated ceramic base plate

Applications

- drives
 - AC
 - DC
- power supplies
 - rectifiers with power factor correction and recuperation capability
 - UPS

Free wheeling diodes D1 - D2

Symbol	Conditions	Maximum Ratings		
I_{F25}	$T_C = 25^\circ C$		450	A
I_{F80}	$T_C = 80^\circ C$		290	A

Symbol **Conditions****Characteristic Values**

	min.	typ.	max.		
V_F	$I_F = 300 A; V_{GE} = 0 V;$ $T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		2.3 1.7	2.7	V V
I_{RM} t_{rr}	$\left\{ \begin{array}{l} I_F = 225 A; dI_F/dt = -2000 A/\mu s; \\ V_R = 600 V; V_{GE} = 0 V; T_{VJ} = 125^\circ C \end{array} \right.$		200 220		A ns
R_{thJC} R_{thJH}	(per IGBT) with heatsink compound		0.3	0.15	K/W K/W

Chopper anti parallel diodes D11 - D12

Symbol	Conditions	Maximum Ratings		
I_{F25}	$T_C = 25^\circ C$		150	A
I_{F80}	$T_C = 80^\circ C$		95	A

Symbol **Conditions****Characteristic Values**

	min.	typ.	max.		
V_F	$I_F = 100 A; V_{GE} = 0 V;$ $T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		2.3 1.7	2.7	V V
I_{RM} t_{rr}	$\left\{ \begin{array}{l} I_F = 75 A; dI_F/dt = -750 A/\mu s; \\ V_R = 600 V; V_{GE} = 0 V; T_{VJ} = 125^\circ C \end{array} \right.$		80 220		A ns
R_{thJC} R_{thJH}	(per IGBT) with heatsink compound		0.9	0.45	K/W K/W

Temperature Sensor NTC (...T version only)

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
R_{25}	$T = 25^\circ C$	$\left\{ R(T) = R_{25} \cdot e^{B_{25/100} \left(\frac{1}{T} - \frac{1}{298K} \right)} \right\}$	2200 3560		k Ω K
$B_{25/100}$					

Module

Symbol	Conditions	Maximum Ratings		
T_{VJ}	operating	-40...+150		°C
T_{stg}		-40...+125		°C
V_{ISO}	$I_{ISOL} \leq 1 mA; 50/60 Hz$	4000		V \sim
M_d	Mounting torque (module, M6) (terminal, M6)	2.25 - 2.75 4.5 - 5.5		Nm Nm

Symbol **Conditions****Characteristic Values**

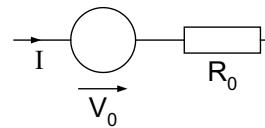
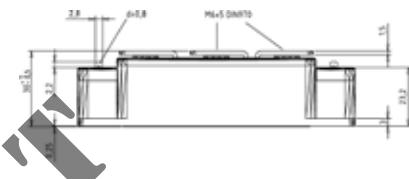
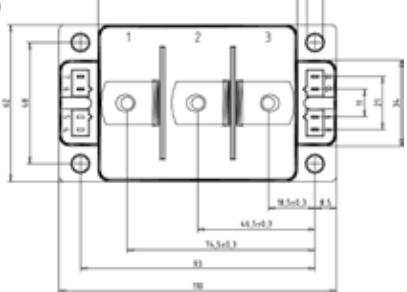
	min.	typ.	max.	
d_s	Creepage distance on surface	2		mm
d_A	Strike distance in air	2		mm
Weight		250		g

IXYS reserves the right to change limits, test conditions and dimensions.

20090812c

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Equivalent Circuits for Simulation**Conduction**IGBT (typ. at $V_{GE} = 15 V; T_J = 125^\circ C$)
 $V_0 = 1.0 V; R_0 = 5.3 m\Omega$ Free Wheeling Diode D1-D2 (typ. at $T_J = 125^\circ C$)
 $V_0 = 1.3 V; R_0 = 1.3 m\Omega$ **Dimensions in mm (1 mm = 0.0394")****Optional accessories for modules**keyed twin plugs
(UL758, style 1385, CSA class 5851, guide 460-1-1)

- Type ZY180L with wire length 350mm
– for pins 11 (yellow wire) and 10 (red wire)
- Type ZY180R with wire length 350mm
– for pins 8 (yellow wire) and 9 (red wire)